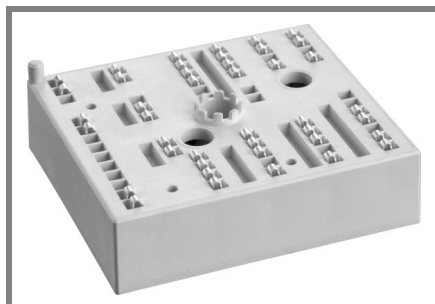


SKiiP 24NAB126V10



MiniSKiiP[®] 2

3-phase bridge rectifier +
brake chopper + 3-phase
bridge inverter
SKiiP 24NAB126V10

Features

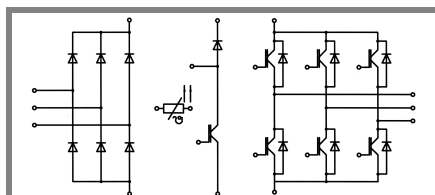
- Fast Trench IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

Typical Applications

- Inverter up to 19 kVA
- Typical motor power 11 kW

Remarks

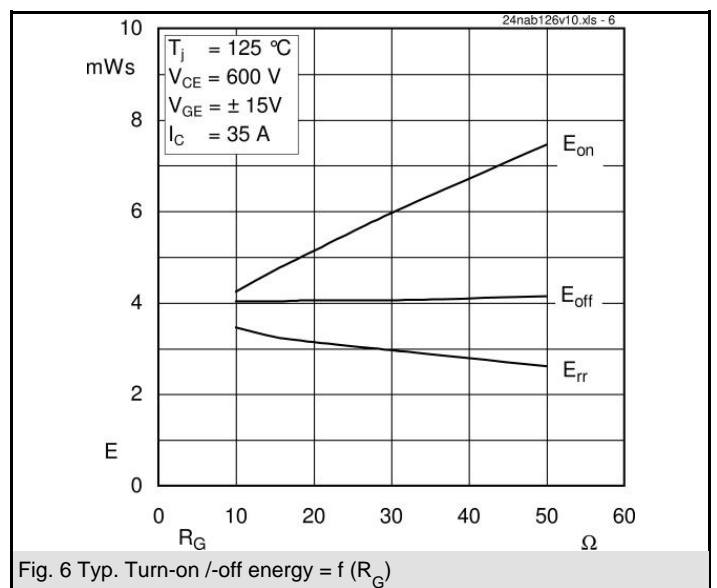
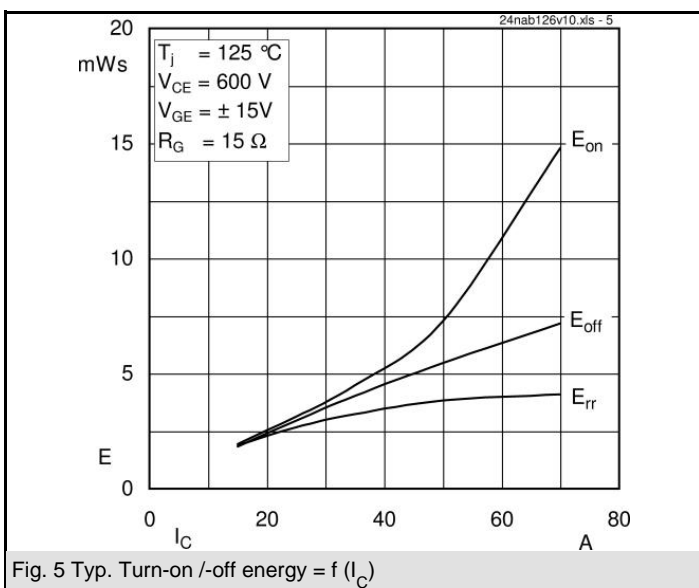
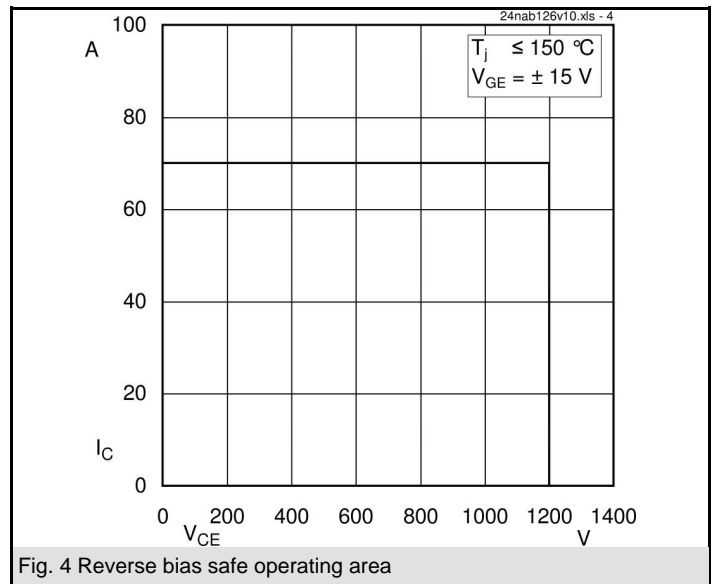
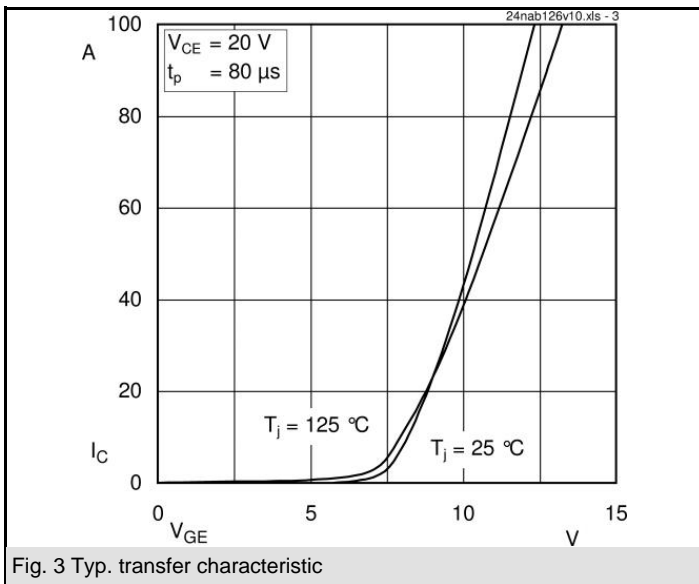
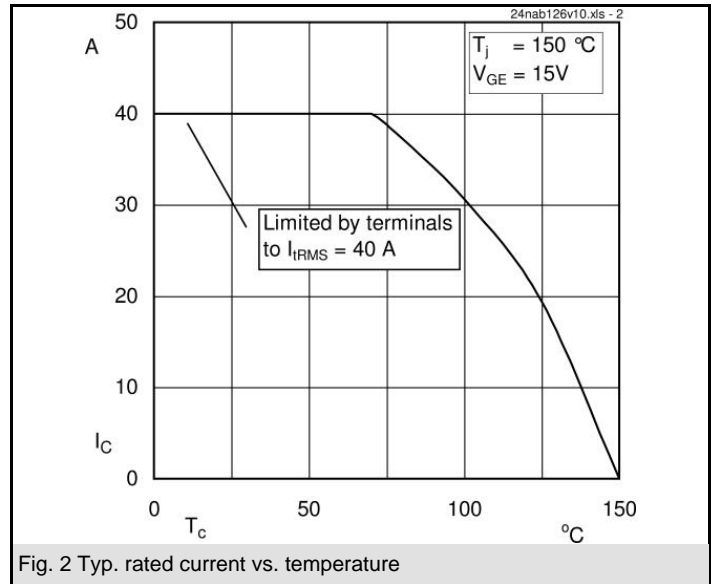
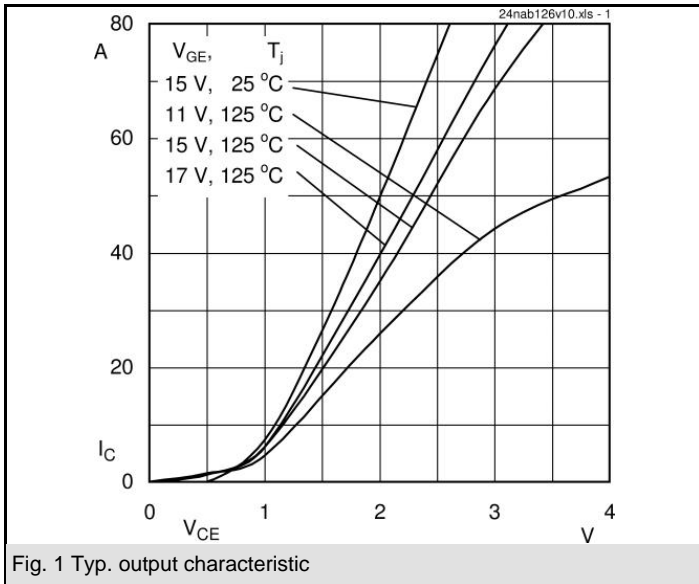
- V_{CEsat} , V_F = chip level value



NAB

Absolute Maximum Ratings		$T_s = 25\text{ °C}$, unless otherwise specified		
Symbol	Conditions	Values	Units	
IGBT - Inverter, Chopper				
V_{CES}	$T_s = 25\text{ (70) °C}$	1200	V	
I_C		52 (40)	A	
I_{CRM}		70	A	
V_{GES}		± 20	V	
T_j		- 40 ... + 150	°C	
Diode - Inverter, Chopper				
I_F	$T_s = 25\text{ (70) °C}$	38 (29)	A	
I_{FRM}		70	A	
T_j		- 40 ... + 150	°C	
Diode - Rectifier				
V_{RRM}	$T_s = 70\text{ °C}$	1600	V	
I_F		61	A	
I_{FSM}		$t_p = 10\text{ ms, sin } 180\text{ °}, T_j = 25\text{ °C}$	700	A
i^2t		$t_p = 10\text{ ms, sin } 180\text{ °}, T_j = 25\text{ °C}$	2400	A ² s
T_j		- 40 ... + 150	°C	
Module				
I_{RMS}	per power terminal (20 A / spring)	40	A	
T_{stg}		- 40 ... + 125	°C	
V_{isol}	AC, 1 min.	2500	V	

Characteristics		$T_s = 25\text{ °C}$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT - Inverter, Chopper					
V_{CEsat}	$I_{Cnom} = 35\text{ A}, T_j = 25\text{ (125) °C}$		1,7 (2)	2,1 (2,4)	V
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 1,5\text{ mA}$	5	5,8	6,5	V
$V_{CE(TO)}$	$T_j = 25\text{ (125) °C}$		1 (0,9)	1,2 (1,1)	V
r_T	$T_j = 25\text{ (125) °C}$		20 (31)	26 (37)	mΩ
C_{ies}	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$		2,4		nF
C_{oes}	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$		0,5		nF
C_{res}	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$		0,3		nF
$R_{th(j-s)}$	per IGBT		0,75		K/W
$t_{d(on)}$	under following conditions		80		ns
t_r	$V_{CC} = 600\text{ V}, V_{GE} = \pm 15\text{ V}$		30		ns
$t_{d(off)}$	$I_{Cnom} = 35\text{ A}, T_j = 125\text{ °C}$		410		ns
t_f	$R_{Gon} = R_{Goff} = 15\text{ Ω}$		120		ns
E_{on}	inductive load		4,6		mJ
E_{off}			4		mJ
Diode - Inverter, Chopper					
$V_F = V_{EC}$	$I_{Fnom} = 35\text{ A}, T_j = 25\text{ (125) °C}$		1,8 (1,8)	2,1 (2,2)	V
$V_{(TO)}$	$T_j = 25\text{ (125) °C}$		1 (0,8)	1,1 (0,9)	V
r_T	$T_j = 25\text{ (125) °C}$		23 (31)	29 (37)	mΩ
$R_{th(j-s)}$	per diode		1,5		K/W
I_{RRM}	under following conditions		43		A
Q_{rr}	$I_{Fnom} = 35\text{ A}, V_R = 600\text{ V}$		7		μC
E_{rr}	$V_{GE} = 0\text{ V}, T_j = 125\text{ °C}$		3,3		mJ
	$di_F/dt = 1450\text{ A/μs}$				
Diode - Rectifier					
V_F	$I_{Fnom} = 35\text{ A}, T_j = 25\text{ °C}$		1,1		V
$V_{(TO)}$	$T_j = 150\text{ °C}$		0,8		V
r_T	$T_j = 150\text{ °C}$		11		mΩ
$R_{th(j-s)}$	per diode		0,9		K/W
Temperature Sensor					
R_{ts}	3 %, $T_r = 25\text{ (100) °C}$		1000(1670)		Ω
Mechanical Data					
w			65		g
M_s	Mounting torque	2		2,5	Nm



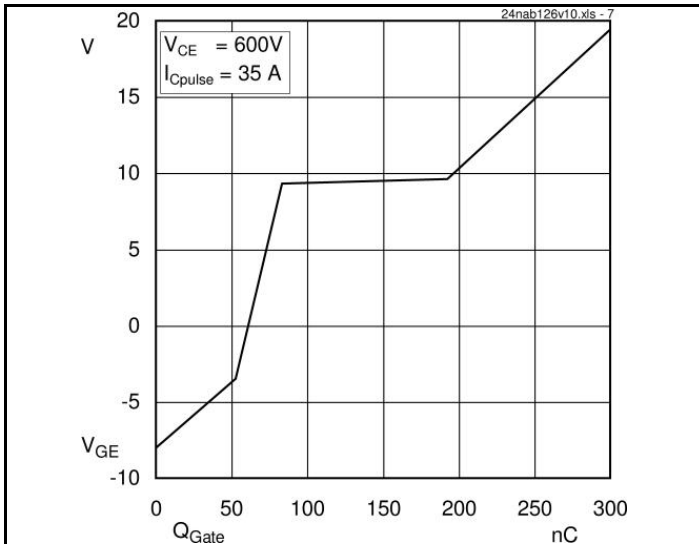


Fig. 7 Typ. gate charge characteristic

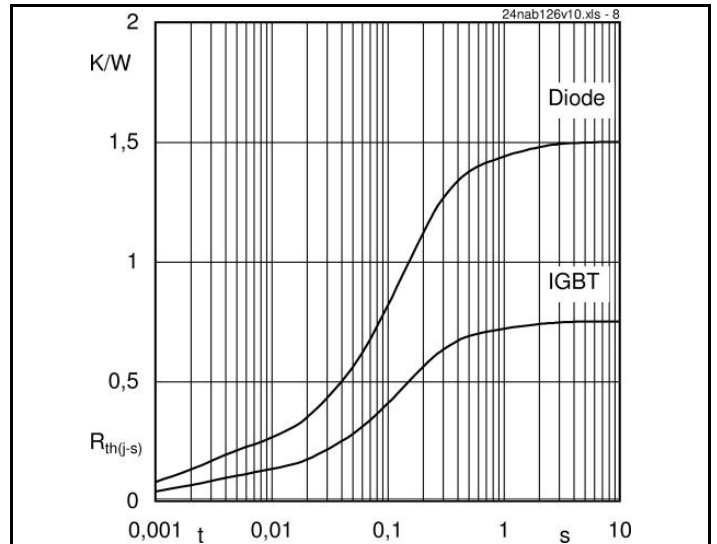


Fig. 8 Typ. thermal impedance

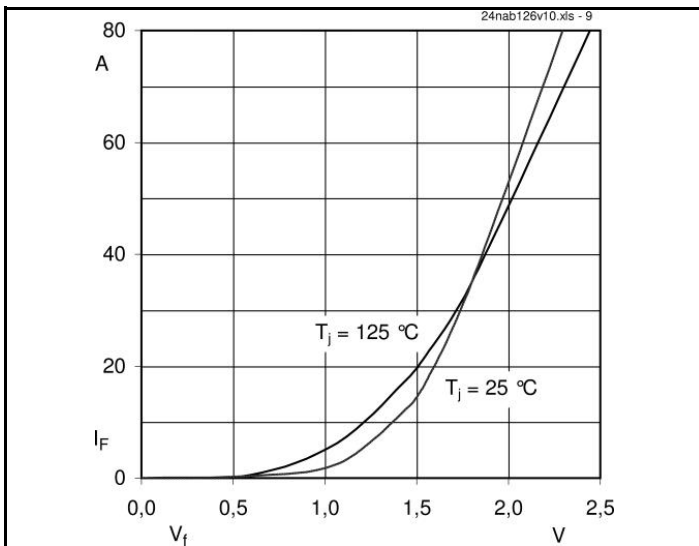


Fig. 9 Typ. freewheeling diode forward characteristic

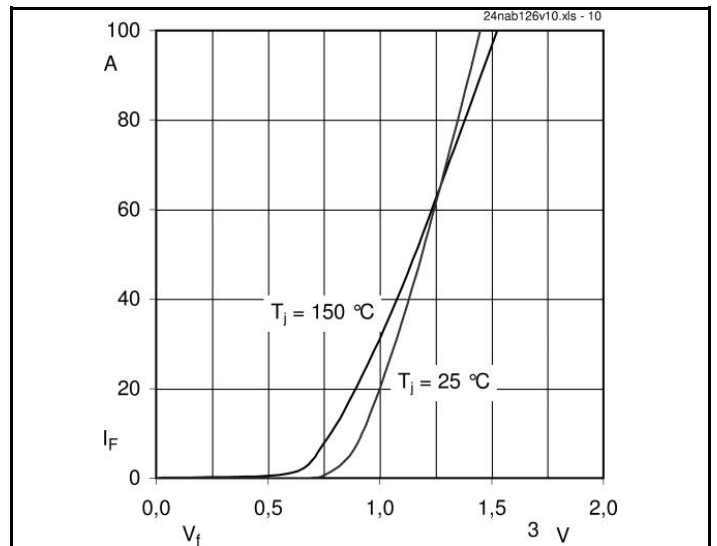
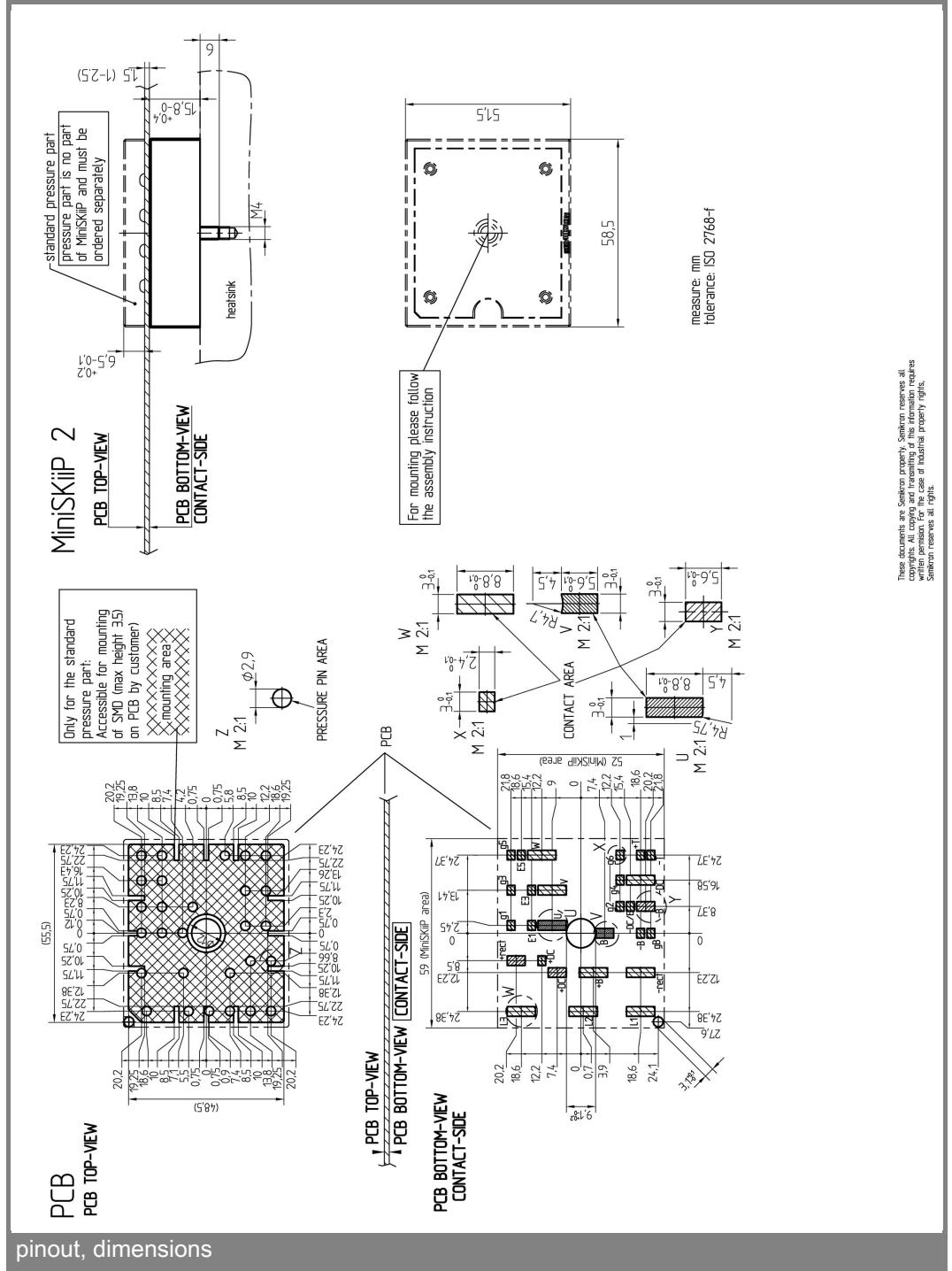
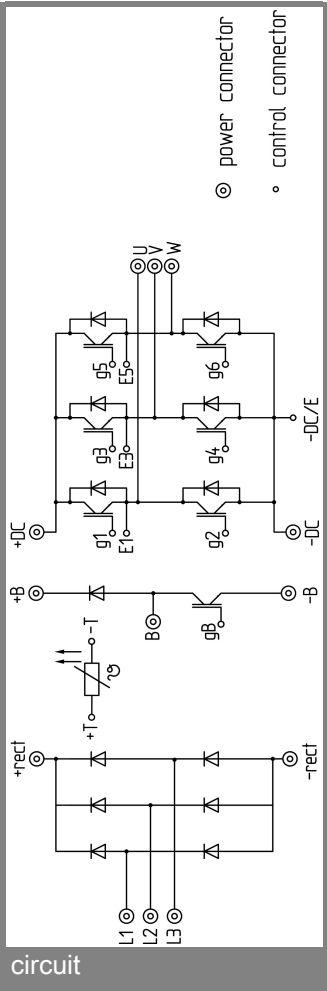


Fig. 10 Typ. input bridge forward characteristic



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